

Jg Correia

List of Publications by Year in descending order

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Version: 2024-02-01

17
papers

317
citations

933447

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h-index

888059

17
g-index

17
all docs

17
docs citations

17
times ranked

350
citing authors

#	ARTICLE	IF	CITATIONS
1	Lattice location of the group V elements As and Sb in ZnO. Physica B: Condensed Matter, 2009, 404, 4803-4806.	2.7	10
2	Lattice location of implanted As in ZnO. Superlattices and Microstructures, 2007, 42, 8-13.	3.1	4
3	Stability and luminescence studies of Tm and Er implanted ZnO single crystals. Nuclear Instruments & Methods in Physics Research B, 2006, 242, 580-584.	1.4	25
4	Lattice sites of implanted Cu and Ag in ZnO. Superlattices and Microstructures, 2006, 39, 229-237.	3.1	20
5	Position-sensitive Si pad detectors for electron emission channeling experiments. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2004, 524, 245-256.	1.6	56
6	PL studies on ZnO single crystals implanted with thulium ions. Superlattices and Microstructures, 2004, 36, 747-753.	3.1	14
7	Lattice site and stability of implanted Ag in ZnO. Physica B: Condensed Matter, 2003, 340-342, 240-244.	2.7	23
8	Emission channeling experiments from the decay of ^{147}Sm in GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 106-110.	3.5	6
9	Lattice location and optical activation of rare earth implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 132-140.	3.5	44
10	Optical doping of ZnO with Tm by ion implantation. Physica B: Condensed Matter, 2003, 340-342, 235-239.	2.7	30
11	Lattice Location of Implanted ^{147}Nd and ^{147}Pm in GaN Using Emission Channeling. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 453-456.	0.8	7
12	Erbium implantation in strontium titanate. Nuclear Instruments & Methods in Physics Research B, 2002, 191, 317-322.	1.4	5
13	High temperature annealing of Er implanted GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 132-135.	3.5	13
14	$\text{Er}^{\text{II}}\text{O}$ clustering and its influence on the lattice sites of Er in Si. Physica B: Condensed Matter, 1999, 273-274, 342-345.	2.7	4
15	Electron emission channeling with position-sensitive detectors. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 744-750.	1.4	43
16	The influence of oxygen on the lattice sites of rare earths in silicon. Journal of Luminescence, 1998, 80, 303-307.	3.1	9
17	Direct Evidence for Stability of Tetrahedral Interstitial Er in Si up to 900°C . Materials Science Forum, 1997, 258-263, 1503-1508.	0.3	4